

RGT8BM65DGTL1

650V 8A Field Stop Trench IGBT

V _{CES}	650V
ا _د	8A
V _{CE(sat) (Typ.)}	1.65V
P _D	62W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Low Switching Loss
- 3) Short Circuit Withstand Time 5µs
- Built in Very Fast & Soft Recovery FRD (RFN - Series)
- 5) Pb free Lead Plating ; RoHS Compliant

Applications

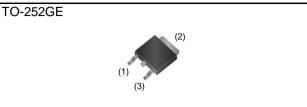
General Inverter

UPS

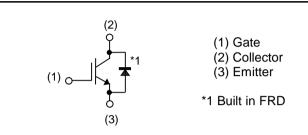
Power Conditioner

Welder

Outline



Inner Circuit



Packaging Specifications

Packaging	Taping
Reel Size (mm)	330
Tape Width (mm)	16
Basic Ordering Unit (pcs)	2,500
Packing code	TL1
Marking	RGT8BM65D
	Tape Width (mm) Basic Ordering Unit (pcs) Packing code

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	12	А
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _C	8	А
Pulsed Collector Current		I _{CP} *1	12	А
Diada Farward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	١ _F	7	А
Diode Forward Current	$T_c = 100^{\circ}C$	١ _F	4	А
Diode Pulsed Forward Current		I _{FP} ^{*1}	12	А
Dower Dissingtion	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	62	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P _D	31	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by T_{jmax.}

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•Thermal Resistance

Parameter	Symbol	Values			Unit
Faranielei		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	2.40	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	9.20	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Daramatar	Symbol Conditions			Unit			
Parameter Symbol Conditions		Conditions	Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA	
Gate - Emitter Leakage Current	I _{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA	
Gate - Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 2.8mA	5.0	6.0	7.0	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 4A, V_{GE} = 15V$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-	1.65 2.1	2.1 -	V	

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deveneter	Symbol Conditions -			1.1		
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	220	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	14	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	4.5	-	
Total Gate Charge	Q_g	V _{CE} = 400V	-	13.5	-	
Gate - Emitter Charge	Q_{ge}	$I_{\rm C} = 4A$	-	4	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	5.5	-	
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 4$ A, $V_{\rm CC} = 400$ V	-	17	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 50\Omega$	-	36	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	69	-	ns
Fall Time	t _f	Inductive Load	-	71	-	
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 4$ A, $V_{\rm CC} = 400$ V	-	17	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 50\Omega$	-	37	-	n 0
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	86	-	ns
Fall Time	t _f	Inductive Load	-	72	-	
		$I_{\rm C} = 12$ A, $V_{\rm CC} = 520$ V		-		
Reverse Bias Safe Operating Area	RBSOA	$V_{P} = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		R _G = 50Ω, T _j = 175°C				
		$V_{CC} \leq 360V$				
Short Circuit Withstand Time	t _{sc}	V _{GE} = 15V	5	-	-	μs
		T _j = 25°C				

•FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Diode Forward Voltage	V _F	$I_F = 4A$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-	1.45 1.4	1.9 -	V	
Diode Reverse Recovery Time	t _{rr}	I _F = 4A	-	40	-	ns	
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/µs	-	4.3	-	А	
Diode Reverse Recovery Charge	Q _{rr}	T _j = 25°C	-	0.09	-	μC	
Diode Reverse Recovery Time	t _{rr}	I _F = 4A	-	94	-	ns	
Diode Peak Reverse Recovery Current	I _{rr}	V _{CC} = 400V di _F /dt = 200A/µs	-	5.4	-	А	
Diode Reverse Recovery Charge	Q _{rr}	T _j = 175°C	-	0.27	-	μC	

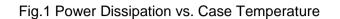


Fig.2 Collector Current vs. Case Temperature

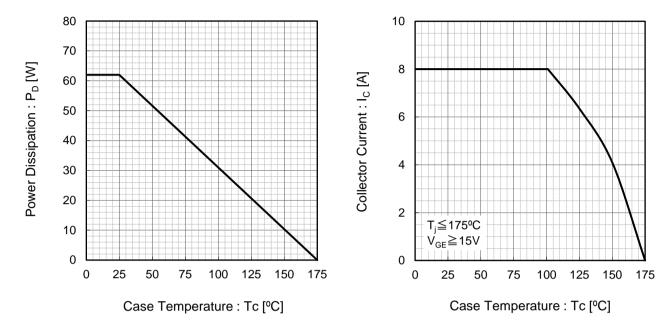
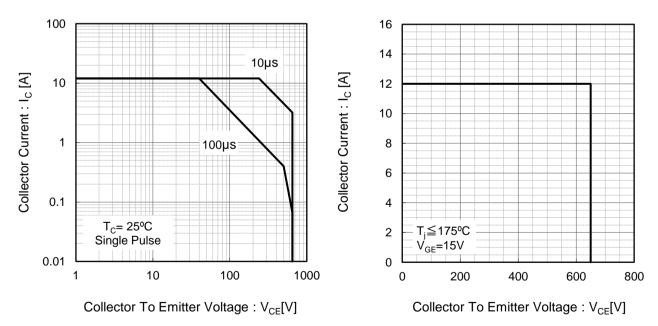


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



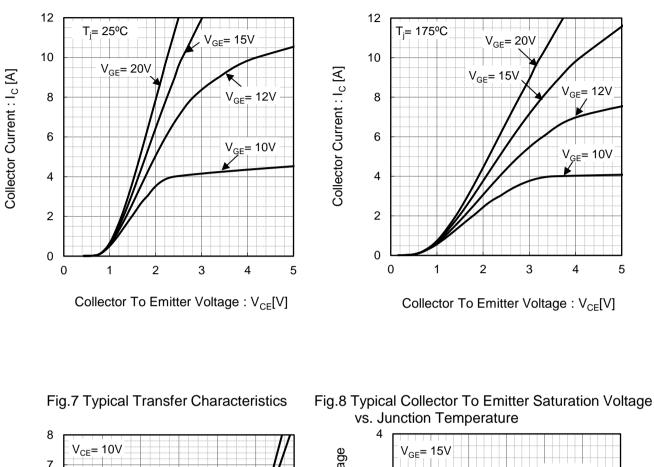
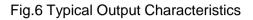


Fig.5 Typical Output Characteristics



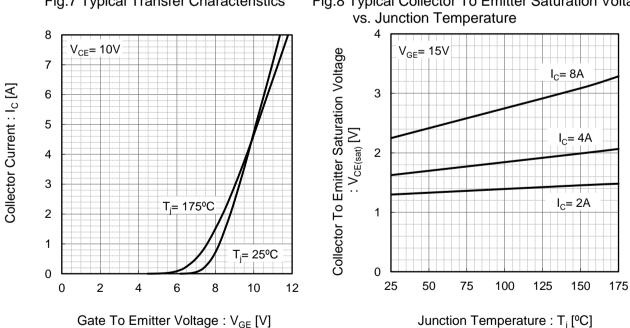


Fig.10 Typical Collector To Emitter Saturation Voltage

•Electrical Characteristic Curves

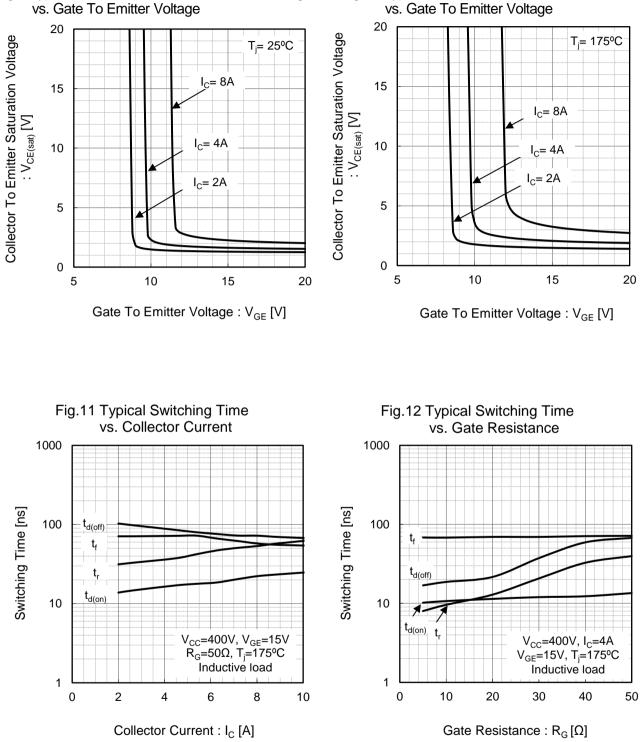
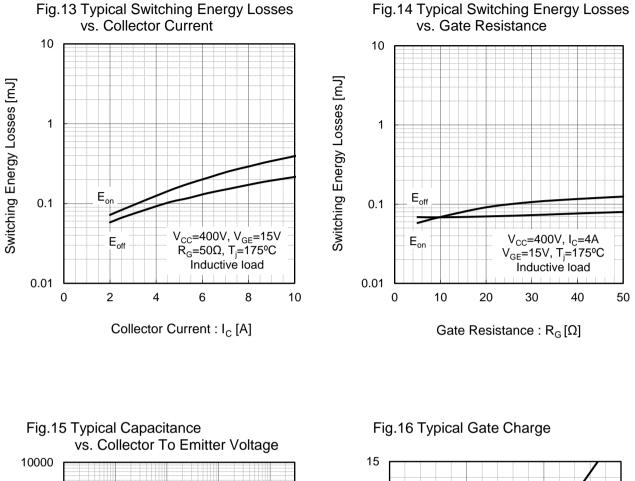
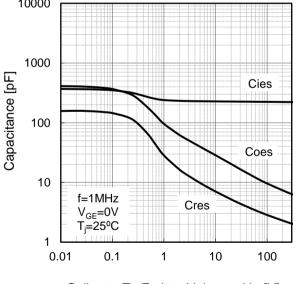
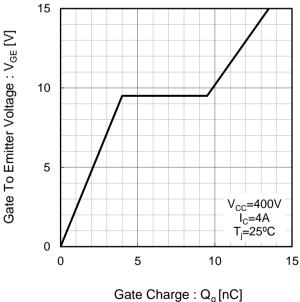


Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage





Collector To Emitter Voltage : V_{CE}[V]



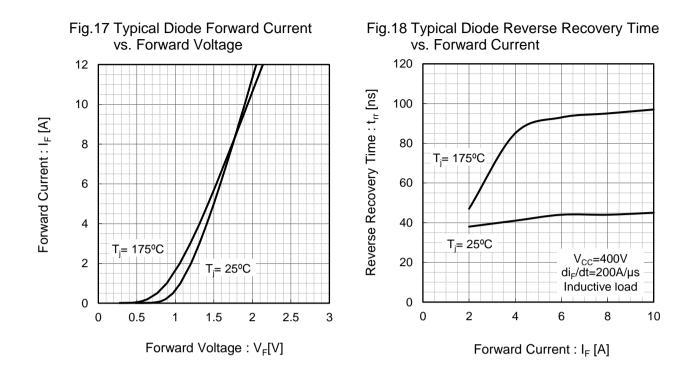


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

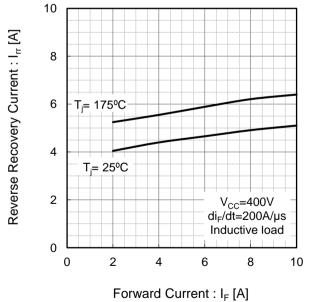
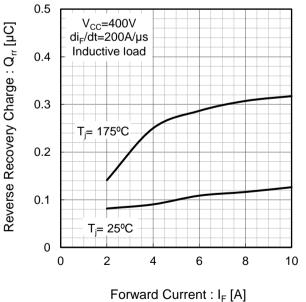


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



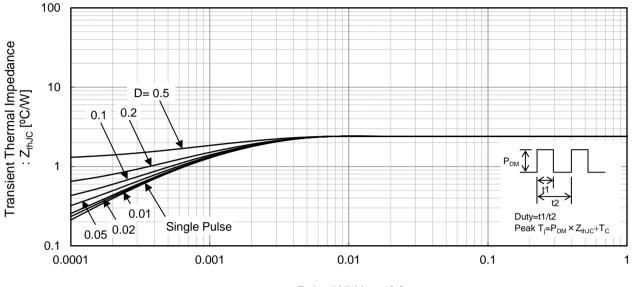


Fig.21 IGBT Transient Thermal Impedance

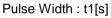
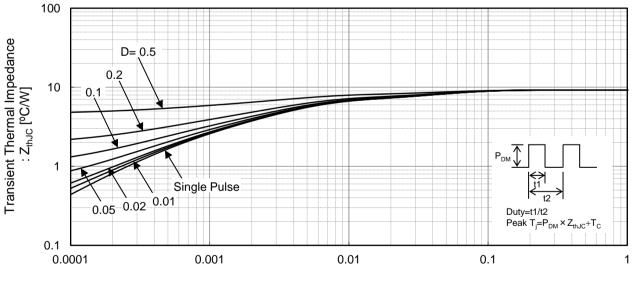


Fig.22 Diode Transient Thermal Impedance



Pulse Width : t1[s]

●Inductive Load Switching Circuit and Waveform

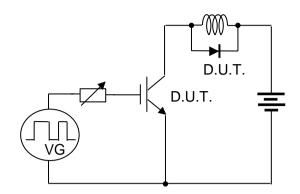


Fig.23 Inductive Load Circuit

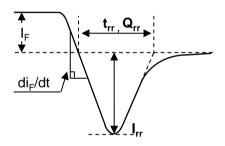


Fig.25 Diode Reverce Recovery Waveform

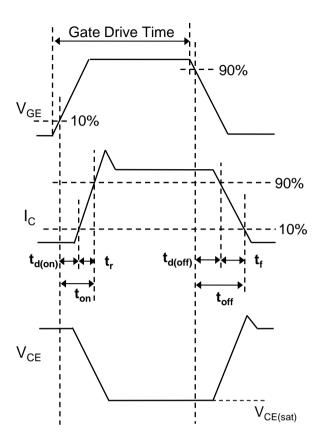


Fig.24 Inductive Load Waveform

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